

crystallizing said amorphous semiconductor film by irradiating said amorphous semiconductor film with a pulsed laser beam;

wherein said laser beam has a pulse width of 200 nsec or more.

21. A method of manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film on an insulating surface;  
providing said semiconductor film with a crystallization promoting material comprising a metal;

crystallizing said amorphous semiconductor film by irradiating said amorphous semiconductor film with a pulsed laser beam having a square shape cross section;

wherein said laser beam has a pulse width of 200 nsec or more, and an irradiation area of said pulsed laser beam is  $10 \text{ cm}^2$  or more.

22. The method according to claim 20 or 21 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Au, Ge, Pb and In.

23. The method according to claim 20 or 21 wherein an energy density of said laser beam at an irradiation area of said semiconductor film is 100 to  $800 \text{ mJ/cm}^2$ .

#### REMARKS

The Official Action mailed July 14, 2000 has been received and its contents carefully studied. Claims 1-19 were pending in the application.

Applicants hereby elect without traverse the Group I claims - that is, claims 1-13, drawn to a method of manufacturing a semiconductor device, classified in class 438, subclass 479+.